

SLAS205B – DECEMBER 1998 – REVISED OCTOBER 2003

- 8-Bit Resolution 80 MSPS Sampling Analog-to-Digital Converter (ADC)
- Low Power Consumption: 165 mW Typ Using External references
- Wide Analog Input Bandwidth: 700 MHz Typ
- 3.3 V Single-Supply Operation
- 3.3 V TTL/CMOS-Compatible Digital I/O
- Internal Bottom and Top Reference Voltages
- Adjustable Reference Input Range
- Power Down (Standby) Mode
- Separate Power Down for Internal Voltage References
- Three-State Outputs
- 28-Pin Small Outline IC (SOIC) and Thin Shrink SOP (TSSOP) Packages
- Applications
 - Digital Communications
 - Flat Panel Displays
 - High-Speed DSP Front-End (TMS320C6000)
 - Medical Imaging
 - Graphics Processing (Scan Rate/Format Conversion)
 - DVD Read Channel Digitization

DESCRIPTION

The TLV5580 is an 8-bit 80 MSPS high-speed A/D converter. It converts the analog input signal into 8-bit binary-coded digital words up to a sampling rate of 80 MHz. All digital inputs and outputs are 3.3 V TTL/CMOS-compatible.

The device consumes very little power due to the 3.3 V supply and an innovative single-pipeline architecture implemented in a CMOS process. The user obtains maximum flexibility by setting both bottom and top voltage references from user-supplied voltages. If no external references are available, on-chip references are available for

DW C	or pw f	PAC	KAGE				
(TOP VIEW)							
1			1				
DRV _{DD}	$ _1 \cup$	28] AV _{SS}				
D0 [2	27] AV _{DD}				
D1 [3	26] AIN				
D2 [4	25] CML				
D3 [5	24	PWDN_REF				
D4 [6	23	AV _{SS}				
D5 [7	22	REFBO				
D6 [8	21] REFBI				
D7 [9	20] REFTI				
DRV _{SS}	10	19] REFTO				
DV _{SS} [11	18	AV _{SS}				
CLK [12	17	BG				
OE [13	16	AV _{DD}				
DV _{DD}	14	15	STBY				
7 10							

internal and external use. The full-scale range is 1 Vpp up to 1.6 Vpp, depending on the analog supply voltage. If external references are available, the internal references can be disabled independently from the rest of the chip, resulting in an even greater power saving.

While usable in a wide variety of applications, the device is specifically suited for the digitizing of high-speed graphics and for interfacing to LCD panels or LCD/DMD projection modules . Other include applications DVD read channel medical digitization, imaging and communications. This device is suitable for IF sampling of communication systems using sub-Nyquist sampling methods because of its high analog input bandwidth.



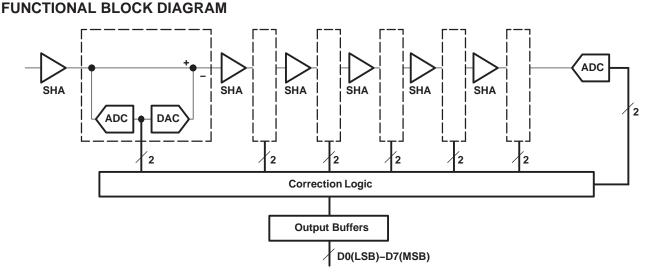
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The single-pipeline architecture uses 6 ADC/DAC stages and one final flash ADC. Each stage produces a resolution of 2 bits. The correction logic generates its result using the 2-bit result from the first stage, 1 bit from each of the 5 succeeding stages, and 1 bit from the final stage in order to arrive at an 8-bit result. The correction logic ensures no missing codes over the full operating temperature range.

PRODUCT	PACKAGE-LEAD	PACKAGE DESIGNATOR ⁽¹⁾	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
TLV5580	SOIC, 28	DW	0°C to +70°C	TLV5580C	TLV5580CDW	Rails, 20
"	"	"	"	"	TLV5580CDWR	Tape and Reel, 1000
TLV5580	TSSOP. 28	PW	0°C to +70°C	TV5580	TLV5580CPW	Rails, 20
"	"	"	"	"	TLV5580CPWR	Tape and Reel, 2000
TLV5580	SOIC, 28	DW	-40°C to +85°C	TLV5580I	TLV5580IDW	Rails, 50
"	"	"	"	"	TLV5580IDWR	Tape and Reel, 1000
TLV5580	TSSOP, 28	PW	-40°C to +85°C	TY5580	TLV5580IPW	Rails, 50
"	"	"	"	"	TLV5580IPWR	Tape and Reel, 2000

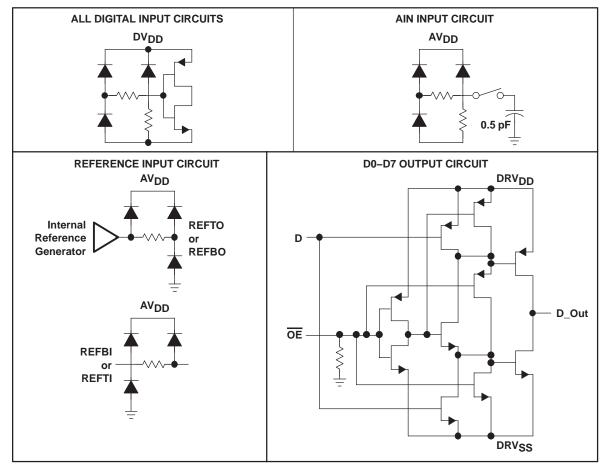
PACKAGE/ORDERING INFORMATION

(1) For the most current specifications and package information, refer to our web site at www.ti.com.



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CIRCUIT DIAGRAMS OF INPUTS AND OUTPUTS





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Terminal Functions

TERMINAL NAME NO.					
		I/O	DESCRIPTION		
AIN	26	I	Analog input		
AVDD	16, 27	1	Analog supply voltage		
AVSS	18, 23, 28	I	Analog ground		
BG	17	0	Band gap reference voltage. A 1 μ F capacitor (with an optional 0.1 μ F capacitor in parallel) should be connected between this terminal and AV _{SS} for external filtering.		
CLK	12	I	Clock input. The input is sampled on each rising edge of CLK.		
CML	25	0	Common mode level. This voltage is equal to $(AV_{DD} - AV_{SS}) \div 2$. An external 0.1 μ F capacitor should be connected between this terminal and AV _{SS} .		
D0 – D7	2 – 9	0	Data outputs. D7 is the MSB		
DRV _{DD}	1	I	Supply voltage for digital output drivers		
DRVSS	10	I	Ground for digital output drivers		
DVDD	14	I	Digital supply voltage		
OE	13	Ι	Output enable. When high the D0 – D7 outputs go in high-impedance mode.		
DVSS	11	I	Digital ground		
PWDN_REF	24	I	Power down for internal reference voltages. A high on this terminal will disable the internal reference circuit.		
REFBI	21	I	Reference voltage bottom input. The voltage at this terminal defines the bottom reference voltage for the ADC. It can be connected to REFBO or to an externally generated reference level. Sufficient filtering should be applied to this input. The use a 0.1 μ F capacitor connected between REFBI and AV _{SS} is recommended. Additionally, a 0.1 μ F capacitor can be connected between REFTI and REFBI.		
REFBO	22	0	Reference voltage bottom output. An internally generated reference is available at this terminal. It can be connected to REFBI or left unconnected. A 1 μ F capacitor between REFBO and AV _{SS} will provide sufficient decoupling required for this output.		
REFTI	20	I	Reference voltage top input. The voltage at this terminal defines the top reference voltage for the ADC. It can be connected to REFTO or to an externally generated reference level. Sufficient filtering should be applied to this input. The use of a 0.1 μ F capacitor between REFTI and AV _{SS} is recommended. Additionally, a 0.1 μ F capacitor can be connected between REFTI and REFBI.		
REFTO	19	0	Reference voltage top output. An internally generated reference is available at this terminal. It can be connected to REFTI or left unconnected. A 1 μ F capacitor between REFTO and AV _{SS} will provide sufficient decoupling required for this output.		
STBY	15	Ι	Standby input. A high level on this input enables a power-down mode.		



ABSOLUTE MAXIMUM RATINGS OVER OPERATING FREE-AIR TEMPERATURE (unless otherwise noted) †

Supply voltage: AV _{DD} to AGND, DV _{DD} to DGND	0.5 V to 0.5 V -0.5 V to DV _{DD} + 0.5 V
Analog input voltage range to AGND	–0.5 V to AV _{DD} + 0.5 V
Digital output voltage applied from external source to DGND	–0.5 V to DV _{DD} + 0.5 V
Reference voltage input range to AGND: V(REFTI), V(REFTO), V(REFBI), V(REFBO)	–0.5 V to AV _{DD} + 0.5 V
Operating free-air temperature range, T _A : TLV5580C	0°C to 70°C
TLV5580I	–40°C to 85°C
Storage temperature range, T _{stg}	–55°C to 150°C

(1) †Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS OVER OPERATING FREE-TEMPERATURE RANGE

POWER SUPPLY

		MIN	NOM	MAX	UNIT
	AVDD				
Supply voltage	DV _{DD}	3	3.3	3.6	V
	DRV _{DD}				

ANALOG AND REFERENCE INPUTS

	MIN	NOM	МАХ	UNIT
Reference input voltage (top), V(REFTI)	(NOM) – 0.2	2 + (AV _{DD} – 3)	(NOM) + 0.2	V
Reference input voltage (bottom), V(REFBI)	0.8	1	1.2	V
Reference voltage differential, V(REFTI) - V(REFBI)			$1 + (AV_{DD} - 3)$	V
Analog input voltage, V(AIN)	V _(REFBI)		V(REFTI)	V

DIGITAL INPUTS

	MIN	NOM MAX	UNIT
High-level input voltage, VIH	2.0	DVDD	V
Low-level input voltage, VIL	DGND	0.2xDV _{DD}	V
Clock period, t _C	12.5		ns
Pulse duration, clock high, t _{w(CLKH)}	5.25		ns
Pulse duration, clock low, tw(CLKL)	5.25		ns



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ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS WITH $F_{CLK} = 80$ MSPS AND USE OF EXTERNAL VOLTAGE REFERENCES (unless otherwise noted)

POWER SUPPLY

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
		AV _{DD}			57	71	
IDD	Operating supply current	DVDD	$AV_{DD} = DV_{DD} = 3.3 \text{ V}, DRV_{DD} = 3 \text{ V},$ $C_1 = 15 \text{ pF}, V_1 = 1 \text{ MHz}, -1 \text{ dBFS}$		3	3.6	mA
		DRV _{DD}			5	7.5	
D	P _D Power dissipation		PWDN_REF = L		213	270	
۳D			PWDN_REF = H		165	210	mW
PD(STBY)	Standby power		STBY = H, CLK held high or low		11	15	

DIGITAL LOGIC INPUTS

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
IIН	High-level input current on CLK [†]	$AV_{DD} = DV_{DD} = DRV_{DD} = CLK = 3.6$ V			10	μΑ
IIL	Low-level input current on digital inputs (OE, STDBY, PWDN_REF, CLK)	$AV_{DD} = DV_{DD} = DRV_{DD} = 3.6 V,$ Digital inputs at 0 V			10	μA
Cl	Input capacitance			5		pF

⁺ I_{IH} leakage current on other digital inputs (OE, STDBY, PWDN_REF) is not measured since these inputs have an internal pull-down resistor of 4 KΩ to DGND.

LOGIC OUTPUTS

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High-level output voltage	$AV_{DD} = DV_{DD} = DRV_{DD} = 3$ V at $I_{OH} = 50 \mu A$, Digital output forced high	2.8			V
V _{OL}	Low-level output voltage	$AV_{DD} = DV_{DD} = DRV_{DD} = 3.6 V at I_{OL} = 50 \mu A$, Digital output forced low			0.1	V
CO	Output capacitance			5		pF
IOZH	High-impedance state output current to high level				10	μΑ
IOZL	High-impedance state output current to low level	$AV_{DD} = DV_{DD} = DRV_{DD} = 3.6 V$			10	μΑ

ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS WITH $F_{CLK} = 80$ MSPS AND USE OF EXTERNAL VOLTAGE REFERENCES (unless otherwise noted)

DC ACCURACY

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Integral nonlinearity (INL), best-fit	Internal references (see Note 1)	$T_A = -40^{\circ}C$ to $85^{\circ}C$	-2.4	±1	2.4	LSB
Differential nonlinearity (DNL)	Internal references (see Note 2)	$T_A = -40^{\circ}C$ to $85^{\circ}C$	-1	±0.6	1.3	LSB
Zero error		See Note 2			5	%FS
Full scale error	$AV_{DD} = DV_{DD} = 3.3 V, DRV_{DD} = 3 V$	See Note 3			5	%FS

Integral nonlinearity refers to the deviation of each individual code from a line drawn from zero to full scale. The point used as zero
occurs 1/2 LSB before the first code transition. The full–scale point is defined as a level 1/2 LSB beyond the last code transition. The deviation
is measured from the center of each particular code to the true straight line between these two endpoints.

- An ideal ADC exhibits code transitions that are exactly 1 LSB apart. DNL is the deviation from this ideal value. Therefore this measure indicates how uniform the transfer function step sizes are. The ideal step size is defined here as the step size for the device under test (i.e., (last transition level first transition level) + (2ⁿ 2)). Using this definition for DNL separates the effects of gain and offset error. A minimum DNL better than –1 LSB ensures no missing codes.
- 3. Zero error is defined as the difference in analog input voltage between the ideal voltage and the actual voltage that will switch the ADC output from code 0 to code 1. The ideal voltage level is determined by adding the voltage corresponding to 1/2 LSB to the bottom reference level. The voltage corresponding to 1 LSB is found from the difference of top and bottom references divided by the number of ADC output levels (256).

Full-scale error is defined as the difference in analog input voltage – between the ideal voltage and the actual voltage – that will switch the ADC output from code 254 to code 255. The ideal voltage level is determined by subtracting the voltage corresponding to 1.5 LSB from the top reference level. The voltage corresponding to 1 LSB is found from the difference of top and bottom references divided by the number of ADC output levels (256).

ANALOG INPUT

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
CI	Input capacitance			4		pF

REFERENCE INPUT ($AV_{DD} = DV_{DD} = DRV_{DD} = 3.6 V$)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
R _{ref}	Reference input resistance			200		Ω
Iref	Reference input current			5		mA

REFERENCE OUTPUTS

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
V(REFTO)	Reference top offset voltage	Absolute min/max values valid	2.07	$2 + [(AV_{DD} - 3) \div 2]$	2.21	V
V _(REFBO)	Reference bottom offset voltage	and tested for AV _{DD} = 3.3 V	1.09	1 + [(AV _{DD} – 3) ÷ 2]	1.21	V



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ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS WITH F_{CLK} = 80 MSPS AND USE OF EXTERNAL VOLTAGE REFERENCES (unless otherwise noted) (continued) DYNAMIC PERFORMANCE[†]

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	f _{in} = 1 MHz	6.2	6.7		
	f _{in} = 4.43 MHz	6.2	6.7		Dite
Effective number of bits, ENOB	f _{in} = 15 MHz		6.4		Bits
	f _{in} = 76 MHz		6.5		
	f _{in} = 1 MHz	39	42		
Circulto total hormonia distortion + noise C//TUD+NI)	f _{in} = 4.43 MHz	39	42		-ID
Signal-to-total harmonic distortion + noise, S/(THD+N)	f _{in} = 15 MHz		40		dB
	f _{in} = 76 MHz		40		
	f _{in} = 1 MHz	-46 -50			
	f _{in} = 4.43 MHz	-45.5	-49		
Total harmonic distortion (THD)	f _{in} = 15 MHz		-44		dB
	f _{in} = 76 MHz		-45.5		
	f _{in} = 1 MHz	48	51		
	f _{in} = 4.43 MHz	48	51		
Spurious free dynamic range (SFDR)	f _{in} = 15 MHz		46		dB
	f _{in} = 76 MHz		48		
Analog input full-power bandwidth, BW	See Note 4		700		MHz
Differential phase, DP	f _{clk} = 40 MHz, f _{in} = 4.43 MHz,		0.8		0
Differential gain, DG	20 IRE amplitude vs. full-scale of 140 IRE		0.6		%

[†] Based on analog input voltage of -1 dBFS referenced to a 1.3 V_{pp} full-scale input range and using the external voltage references at $f_{clk} = 80$ MSPS with AV_{DD} = DV_{DD} = 3.3 V and DRV_{DD} = 3.0 V at 25°C.

4. The analog input bandwidth is defined as the maximum frequency of a –1 dBFS input sine that can be applied to the device for which an extra 3 dB attenuation is observed in the reconstructed output signal.



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ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS WITH F_{CLK} = 80 MSPS AND USE OF EXTERNAL VOLTAGE REFERENCES (unless otherwise noted) (continued)

TIMING REQUIREMENTS

	PARAMETER	TES	T CONDITIONS	MIN	TYP	MAX	UNIT
fclk	Maximum conversion rate			80			MHz
fclk	Minimum conversion rate					10	kHz
^t d(o)	Output delay time (see Figure 1)	C _L = 10 pF,	See Notes 5 and 6		4.5	9	ns
^t h(o)	Output hold time	C _L = 2 pF,	See Note 5	2			ns
^t d(pipe)	Pipeline delay (latency)	See Note 6		4.5	4.5	4.5	CLK cycles
^t d(a)	Aperture delay time				3		ns
^t j(a)	Aperture jitter	See Note 5			1.5		ps, rms
^t dis	Disable time, OE rising to Hi-Z				5	8	ns
t _{en}	Enable, \overline{OE} falling to valid data				5	8	ns

 Output timing t_{d(0)} is measured from the 1.5 V level of the CLK input falling edge to the 10%/90% level of the digital output. The digital output load is not higher than 10 pF.

Output hold time $t_{h(0)}$ is measured from the 1.5 V level of the CLK input falling edge to the 10%/90% level of the digital output. The digital output is load is not less than 2 pF.

Aperture delay $t_{d(A)}$ is measured from the 1.5 V level of the CLK input to the actual sampling instant.

The OE signal is asynchronous.

OE timing t_{dis} is measured from the $V_{IH(MIN)}$ level of OE to the high-impedance state of the output data. The digital output load is not higher than 10 pF.

OE timing t_{en} is measured from the V_{IL(MAX)} level of OE to the instant when the output data reaches V_{OH(min)} or V_{OL(max)} output levels. The digital output load is not higher than 10 pF.

6. The number of clock cycles between conversion initiation on an input sample and the corresponding output data being made available from the ADC pipeline. Once the data pipeline is full, new valid output data is provided on every clock cycle. In order to know when data is stable on the output pins, the output delay time t_{d(0)} (i.e., the delay time through the digital output buffers) needs to be added to the pipeline latency. Note that since the max. t_{d(0)} is more than 1/2 clock period at 80 MHz; data cannot be reliably clocked in on a rising edge of CLK at this speed. The falling edge should be used.

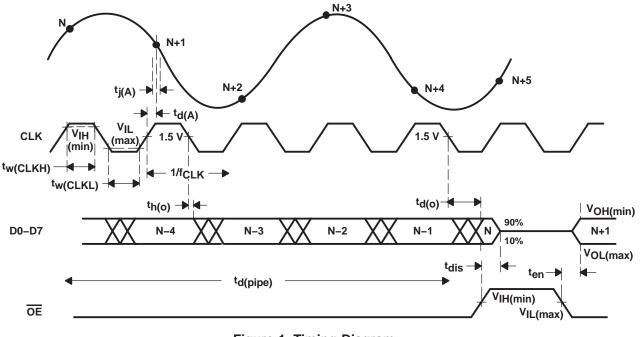
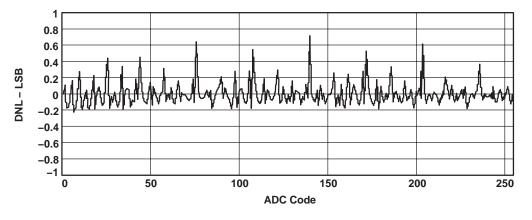


Figure 1. Timing Diagram



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PERFORMANCE PLOTS AT 25°C





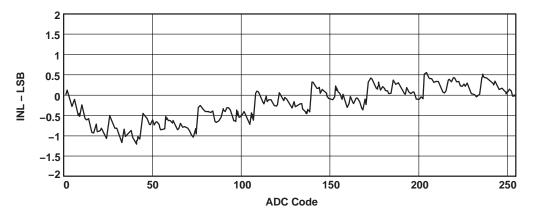


Figure 3. INL vs Input Code At 80 MSPS (With External Reference, PW Package)



PERFORMANCE PLOTS AT 25°C (Continued)

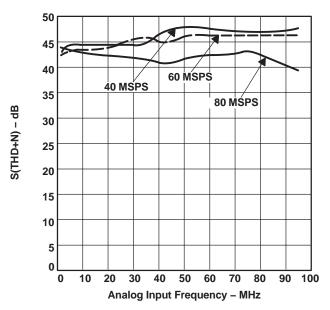


Figure 4. S/(THD+N) vs V_{IN} At 80 MSPS (Internal Reference), 60 MSPS (External Reference), 40 MSPS (External Reference)

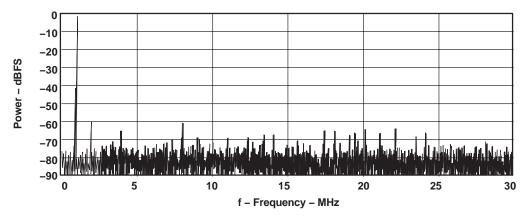
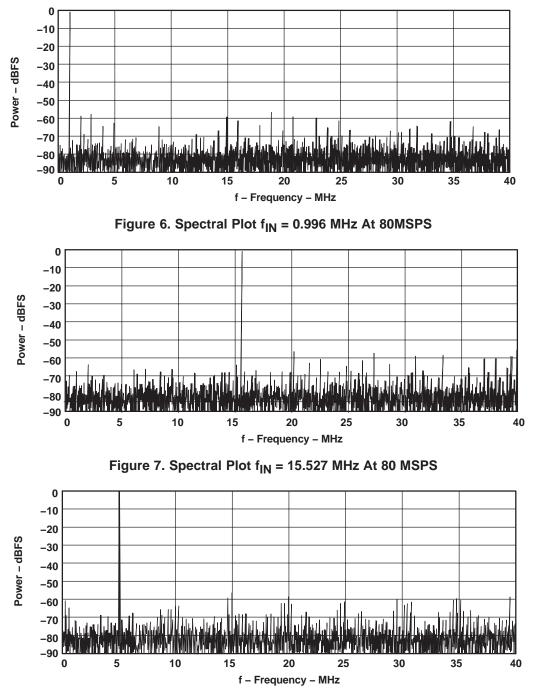
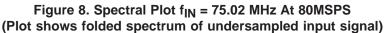


Figure 5. Spectral Plot f_{IN} = 1.011 MHz At 60 MSPS



PERFORMANCE PLOTS AT 25°C (Continued)







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PERFORMANCE PLOTS AT 25°C (Continued)

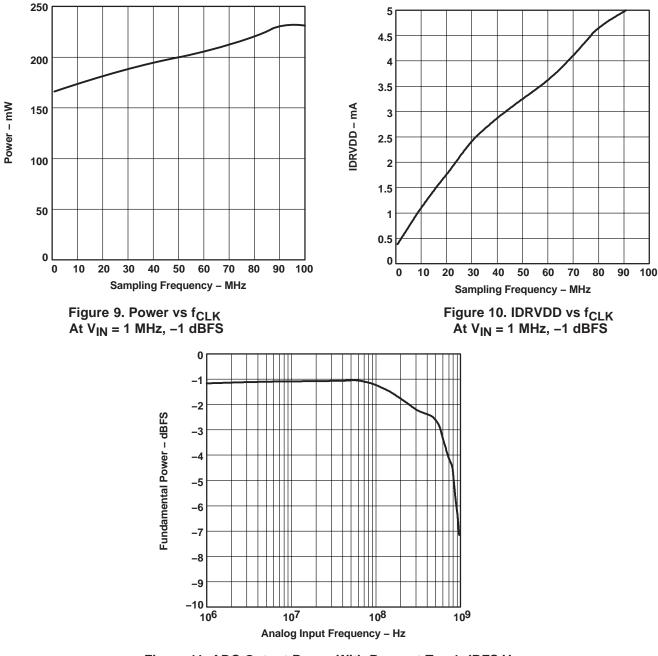
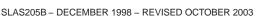


Figure 11. ADC Output Power With Respect To –1 dBFS V_{IN} (Internal Reference, DW Package)





PRINCIPLE OF OPERATION

The TLV5580 implements a high-speed 80 MSPS converter in a cost-effective CMOS process. Powered from 3.3 V, the single-pipeline design architecture ensures low-power operation and 8 bit accuracy. Signal input and clock signals are all single-ended. The digital inputs are 3.3 V TTL/CMOS compatible. Internal voltage references are included for both bottom and top voltages. Therefore the converter forms a self-contained solution. Alternatively the user may apply externally generated reference voltages. In doing so, both input offset and input range can be modified to suit the application.

A high-speed sampling-and-hold captures the analog input signal. Multiple stages will generate the output code with a pipeline delay of 4.5 CLK cycles. Correction logic combines the multistage data and aligns the 8-bit output word. All digital logic operates at the rising edge of CLK.

ANALOG INPUT

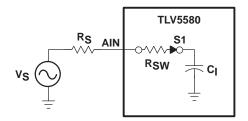


Figure 12. Simplified Equivalent Input Circuit

A first-order approximation for the equivalent analog input circuit of the TLV5580 is shown in Figure 12. The equivalent input capacitance C_I is 4 pF typical. The input must charge/discharge this capacitance within the sample period of one half clock cycle. When a full-scale voltage step is applied, the input source provides the charging current through the switch resistance R_{SW} (200 Ω) of S1 and quickly settles. In this case the input impedance is low. Alternatively, when the source voltage equals the value previously stored on C_I , the hold capacitor requires no input current and the equivalent input impedance is very high.

To maintain the frequency performance outlined in the specifications, the total source impedance should be limited to about 80 Ω , as follows from the equation with f_{CLK} = 80 MHz, C_I = 4 pF, R_{SW} = 200 Ω :

$$R_{S} < \left[1 \div \left(2f_{CLK} \times C_{I} \times In(256)\right) - R_{SW}\right]$$

So, for applications running at a lower f_{CLK}, the total source resistance can increase proportionally.



PRINCIPLE OF OPERATION

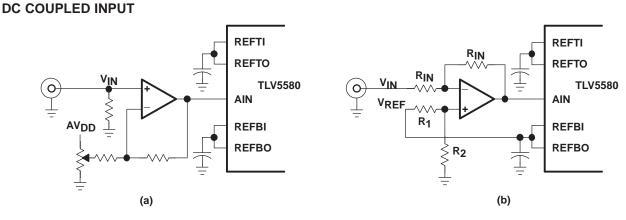
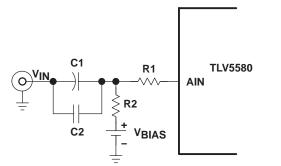


Figure 13. DC-Coupled Input Circuit

For dc-coupled systems an op amp can level-shift a ground-referenced input signal. A circuit as shown in Figure 13(a) is acceptable. Alternatively, the user might want a bipolar shift together with the bottom reference voltage as seen in Figure 13(b). In this case the AIN voltage is given by:

AIN =
$$2 \times R_2 \div (R_1 + R_2) \times V_{REF} - V_{IN}$$

AC COUPLED INPUT





For many applications, especially in single supply operation, ac coupling offers a convenient way for biasing the analog input signal at the proper signal range. Figure 14 shows a typical configuration. To maintain the outlined specifications, the component values need to be carefully selected. The most important issue is the positioning of the 3 dB high-pass corner point $f_{-3 dB}$, which is a function of R_2 and the parallel combination of C_1 and C_2 , called C_{eq} . This is given by the following equation:

$$f_{-3 dB} = 1 \div (2\pi x R_2 x C_{eq})$$

where C_{eq} is the parallel combination of C_1 and C_2 .

Since C1 is typically a large electrolytic or tantalum capacitor, the impedance becomes inductive at higher frequencies. Adding a small ceramic or polystyrene capacitor, C2 of approximately 0.01 μ F, which is not inductive within the frequency range of interest, maintains low impedance. If the minimum expected input signal frequency is 20 kHz, and R2 equals 1 k Ω and R1 equals 50 Ω , the parallel capacitance of C1 and C2 must be a minimum of 8 nF to avoid attenuating signals close to 20 kHz.



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PRINCIPLE OF OPERATION

REFERENCE TERMINALS

The voltages on terminals REFBI and REFTI determine the TLV5580's input range. Since the device has an internal voltage reference generator with outputs available on REFBO respectively REFTO, corresponding terminals can be directly connected externally to provide a contained ADC solution. Especially at higher sampling rates, it is advantageous to have a wider analog input range. The wider analog input range is achievable by using external voltage references (e.g., at AVDD = 3.3 V, the full scale range can be extended from 1 Vpp (internal reference) to 1.3 Vpp (external reference) as shown in Table 1). These voltages should not be derived via a voltage divider from a power supply source. Instead, use a bandgap-derived voltage references to derive both references via an op amp circuit. Refer to the schematic of the TLV5580 evaluation module for an example circuit.

When using external references, the full-scale ADC input range and its dc position can be adjusted. The full-scale ADC range is always equal to $V_{REFT} - V_{REFB}$. The maximum full-scale range is dependent on AV_{DD} as shown in the specification section. In addition to the limitation on their difference, V_{REFT} and V_{REFB} each also have limits on their useful range. These limits are also dependent on AV_{DD} . Table 3 summarizes these limits for 3 cases.

AV _{DD}	V _{REFB} (min)	V _{REFB(max)}	V _{REFT} (min)	V _{REFT(max)}	[VREFT-VREFB]max
3 V	0.8 V	1.2 V	1.8 V	2.2 V	1 V
3.3 V	0.8 V	1.2 V	2.1 V	2.5 V	1.3 V
3.6 V	0.8 V	1.2 V	2.4 V	2.8 V	1.6 V

Table 1. Recommended Operating Modes

DIGITAL INPUTS

The digital inputs are CLK, STDBY, PWDN_REF, and \overline{OE} . All these signals, except CLK, have an internal pull-down resistor to connect to digital ground. This provides a default active operation mode using internal references when left unconnected.

The CLK signal at high frequencies should be considered as an analog input. Overshoot/undershoot should be minimized by proper termination of the signal close to the TLV5580. An important cause of performance degradation for a high-speed ADC is clock jitter. Clock jitter causes uncertainty in the sampling instant of the ADC, in addition to the inherent uncertainty on the sampling instant caused by the part itself, as specified by its aperture jitter. There is a theoretical relationship between the frequency (f) and resolution (2^{N}) of a signal that needs to be sampled and the maximum amount of aperture error dt_{max} that is tolerable. The following formula shows the relation:

$$dt_{max} = 1 \div \left[\pi f 2^{\left(N+1\right)}\right]$$

As an example, for an 8-bit converter with a 15-MHz input, the jitter needs to be kept <41 pF in order not to have changes in the LSB of the ADC output due to the total aperture error.



PRINCIPLE OF OPERATION

DIGITAL OUTPUTS

The output of TLV5580 is a standard binary code. Capacitive loading on the output should be kept as low as possible (a maximum loading of 10 pF is recommended) to provide best performance. Higher output loading causes higher dynamic output currents and can increase noise coupling into the device's analog front end. To drive higher loads, use an output buffer is recommended.

When clocking output data from TLV5580, it is important to observe its timing relation to CLK. Pipeline ADC delay is 4.5 clock cycles to which the maximum output propagation delay is added. See Note 6 in the specification section for more details.

LAYOUT, DECOUPLING AND GROUNDING RULES

It is necessary for any PCB using the TLV5580 to have proper grounding and layout to achieve the stated performance. Separate analog and digital ground planes that are spliced underneath the device are advisable. TLV5580 has digital and analog terminals on opposite sides of the package to make proper grounding easier. Since there is no internal connection between analog and digital grounds, they have to be joined on the PCB. Joining the digital and analog grounds at a point in close proximity to the TLV5580 is advised.

As for power supplies, separate analog and digital supply terminals are provided on the device (AV_{DD}/DV_{DD}) . The supply to the digital output drivers is kept separate also (DRV_{DD}) . Lowering the voltage on this supply from the nominal 3.3 V to 3 V improves performance because of the lower switching noise caused by the output buffers.

Due to the high sampling rate and switched-capacitor architecture, TLV5580 generates transients on the supply and reference lines. Proper decoupling of these lines is essential. Decoupling as shown in the schematic of the TLV5580 EVM is recommended.



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TLV5580 EVALUATION MODULE

TLV5580 EVALUATION MODULE

TI provides an evaluation module (EVM) for TLV5580. The EVM also includes a 10-bit 80 MSPS DAC so that the user can convert the digitized signal back to the analog domain for functional testing. Performance measurements can be done by capturing the ADC's output data.

The EVM provides the following additional features:

- Provision of footprint for the connection of an onboard crystal oscillator, instead of using an external clock input.
- Use of TLV5580 internal or external voltage references. In the case of external references, an onboard circuit
 is used that derives adjustable bottom and top reference voltages from a bandgap reference. Two potentiometers
 allow for the independent adjustments of both references. The full scale ADC range can be adjusted to the input
 signal amplitude.
- All digital output, control signal I/O (output enable, standby, reference power-down) and clock I/O are provided on a single connector. The EVM can thus be part of a larger (DSP) system for prototyping.
- Onboard prototyping area with analog and digital supply and ground connections.

Figure 15 shows the EVM schematic.

- The EVM is factory shipped for use in the following configuration:
- Use of external (onboard) voltage references
- External clock input

ANALOG INPUT

A signal in the range between $V_{(REFBI)}$ and $V_{(REFTI)}$ should be applied to avoid overflow/underflow on connector J10. This signal is onboard terminated with 50 Ω . There is no onboard biasing of the signal. When using external (onboard) references, these levels can be adjusted with R7 ($V_{(REFTI)}$) and R6 ($V_{(REFBI)}$). Adjusting R7 causes both references to shift. R6 only impacts the bottom reference. The range of these signals for which the device is specified depends on AV_{DD} and is shown under the Recommended Operating Conditions.

Internally generated reference levels are also dependent on AV_{DD} as shown in the electrical characteristics section.

CLOCK INPUT

A clock signal should be applied with amplitudes ranging from 0 to AV_{DD} with a frequency equal to the desired sampling frequency on connector J9. This signal is onboard terminated with 50 Ω . Both ADC and DAC run off the same clock signal. Alternatively the clock can be applied from terminal 1 on connector J11. A third option is using a crystal oscillator. The EVM board provides the footprint for a crystal oscillator that can be populated by the end-user, depending on the desired frequency. The footprint is compatible with the Epson EG-8002DC series of programmable high-frequency crystal oscillators. Refer to the TLV5580 EVM Settings for selecting between the different clock modes.

TLV5580 EVALUATION MODULE

POWER SUPPLIES

The board provides seven power supply connectors (see Table 2). For optimum performance, analog and digital supplies should be kept separate. Using separate supplies for the digital logic portion of TLV5580 (DV_{DD}) and its output drivers (DRV_{DD}) benefits dynamic performance, especially when DRV_{DD} is put at the minimum required voltage (3 V), while DV_{DD} might be higher (up to 3.6 V). This lowers the switching noise on the die caused by the output drivers.

SIGNAL NAME	CONNECTOR	BOARD LABEL	DESCRIPTION
DRV3	J1	3DRV	3.3 V digital supply for TLV5580 (digital output drivers)
DV3	J2	3VD	3.3 V digital supply for TLV5580 (digital logic) and peripherals
DV5	J3	5VD	5 V digital supply for D/A converter and peripherals
AV3	J4	3VA	3.3 V analog supply for TLV5580
AV5	J5	5VA	5 V analog supply for onboard reference circuit and D/A converter. Can be left unconnected if internal references are used and no D/A conversion is required.
AV+12	J6	12VA	12 V analog supply for onboard reference circuit. Can be left unconnected if internal references are used.
AV-12	J7	-12VA	-12 V analog supply for onboard reference circuit. Can be left unconnected if internal references are used.

Table 2. Power Supplies

VOLTAGE REFERENCES

SW1 and SW2 switch between internal and external top and bottom references respectively. The external references are onboard generated from a stable bandgap-derived 3.3 V signal (using TI's TPS7133 and quad-op amp TLE2144). They can be adjusted via potentiometers R6 ($V_{(REFBI)}$) and R7 ($V_{(REFTI)}$). It is advised to power down the internal voltage references by asserting PWN_REF when onboard references are used.

The references are measured at test points TP3 (V_(REFB)) and TP4 (V_(REFT)).

DAC OUTPUT

The onboard DAC is a 10-bit 80 MSPS converter. It is connected back-to-back to the TLV5580. While the user could use its analog output for measurements, the DAC output is directly connected to connector J8 and does not pass through an analog reconstruction filter. So mirror spectra from aliased signal components feed through into the analog output.

For this reason and to separate ADC and DAC contributions, performance measurements should be made by capturing the ADC output data available on connector J11 and not by evaluating the DAC output.



TLV5580 EVALUATION MODULE

TLV5580 EVM SETTINGS

CLOCK INPUT SETTINGS

REFERENCE DESIGNATOR	FUNCTION
W1	Clock selection switch 1–2 J11: clock from pin1 on J11 connector 2–3 J9: clock from J9 SMA connector
W2	Clock source switch ■ XTL: clock from onboard crystal oscillator
	□ CLK: clock from pin 1 on J11 connector (if W1/1–2) or J9 SMA connector (if W1/2–3) NOTE: If set to XTL and a XTL oscillator is populated, no clock signal should be applied to J9 or J11, depending on the W1 setting.
W3	Clock output switch 1–2 Rising: clock output on J11 connector is the same phase as the clock to the digital output buffer. Data changes on rising CLK edge.
	2–3 Falling: clock output on J11 connector is the opposite phase as the digital output buffer. Data changes on falling CLK edge.
REFERENCE	
REFERENCE DESIGNATOR	FUNCTION
SW1	REFT external/internal switch ■□ REFT internal: REFT from TLV5580 internal reference
	□ ■ REFT external: REFT from onboard voltage reference circuit
SW2	REFB external/internal switch ■ REFB internal: REFB from TLV5580 internal reference
	□ REFB external: REFB from onboard voltage reference circuit
CONTROL SE	
REFERENCE DESIGNATOR	FUNCTION
W4	TLV5580 and digital output buffer output enable control (1) ■ 5580-574 OE-connected: Connects OEs of TLV5580 and digital output buffer (574 buffer). Use this when no board-external OE is used. In addition, close W5 to have both OEs permanently enabled.
	□ 5580-574 OE-disconnected: Disconnects OEs of TLV5580 and digital output buffer (574 buffer). The OE for the output buffer needs to be pulled low from pin 5 on J11 connector to enable. The OE for TLV5580 is independently controlled from pin 7 on J11 connector (W5 open) or is permanently enabled if W5 is closed.
W5	TLV5580 and digital output buffer output enable control (2) ■ 5580 OE to GND: Connects OEs of TLV5580 to GND. Additionally connects OE of 74ALS574 to GND if W4 is 5580-574 OE-connected.
	\Box 5580 \overline{OE} external: Enables control of \overline{OE} of TLV5580 via pin 7 on J11 connector. When taken high (internal pulldown) the output can be disabled.
W6	TLV5580 STDBY control
	■ Stdby: STDBY is active (high).



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TLV5580 EVALUATION MODULE

CONTROL SETTINGS (Continued)

REFERENCE DESIGNATOR	FUNCTION						
W7	TLV5580 PWDN REF control ■ Pwdn_ref: PWDN_REF is active (high).						
□ Active: PWDN_REF is low, via internal pulldown. PWDN_REF can be taken high from pin 10 on J11 connector to e pwdn_ref mode.							
W8	DAC enable ■ Active: D/A on						
	□ Standby: D/A off						



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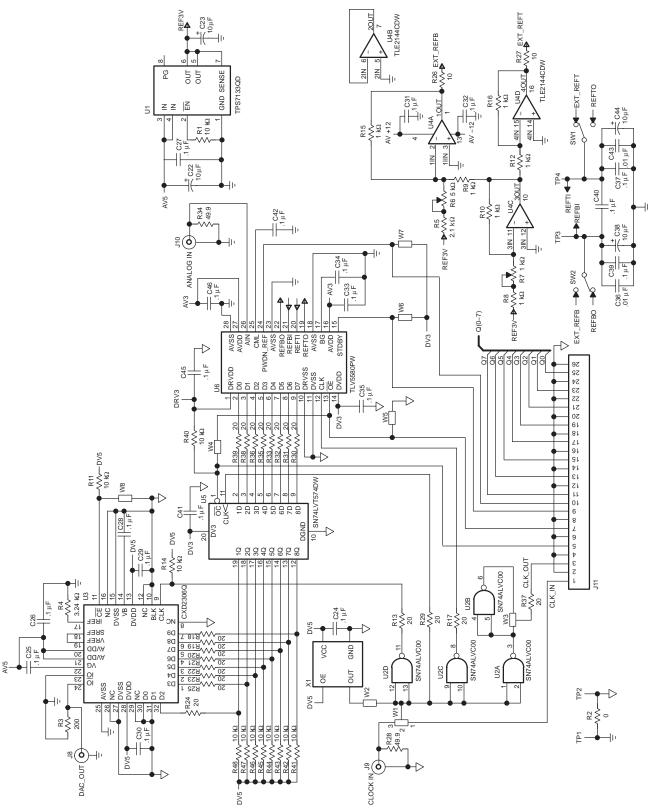
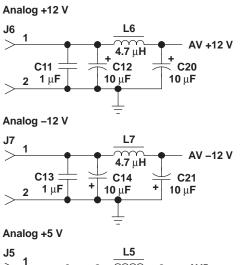
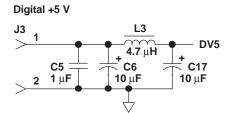


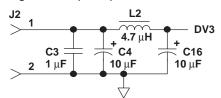
Figure 15. EVM Schematic

TLV5580 EVALUATION MODULE

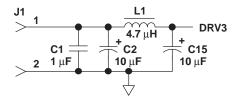


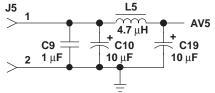


Digital +3.3 V (DVDD)



Digital +3.3 V (DRVDD)





Analog +3.3 V

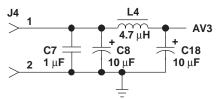
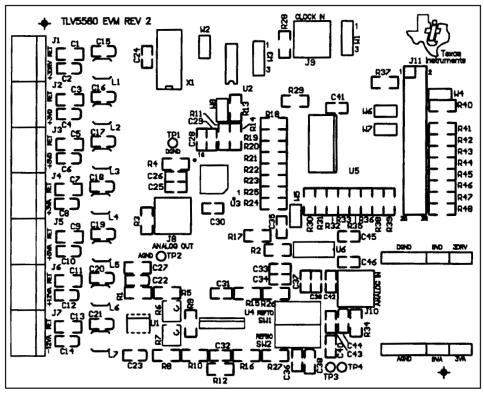


Figure 15. EVM Schematic (Continued)

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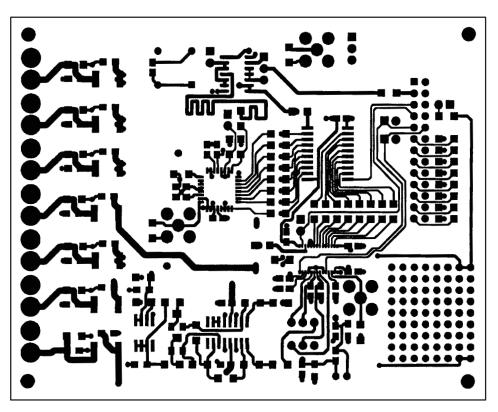


Top Overlay

Figure 15. EVM Schematic (Continued)







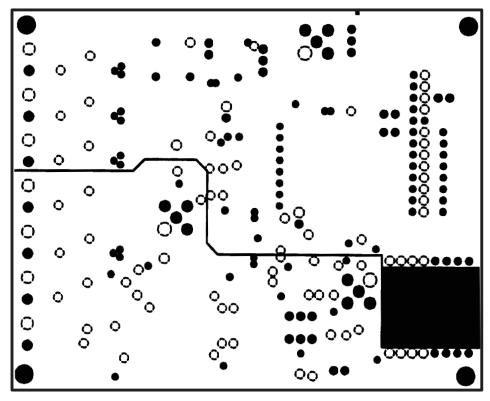
Top Layer

Figure 15. EVM Schematic (Continued)



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TLV5580 EVALUATION MODULE

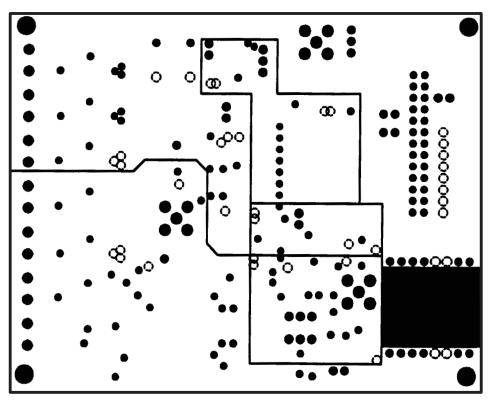


Internal Plane 1

Figure 15. EVM Schematic (Continued)







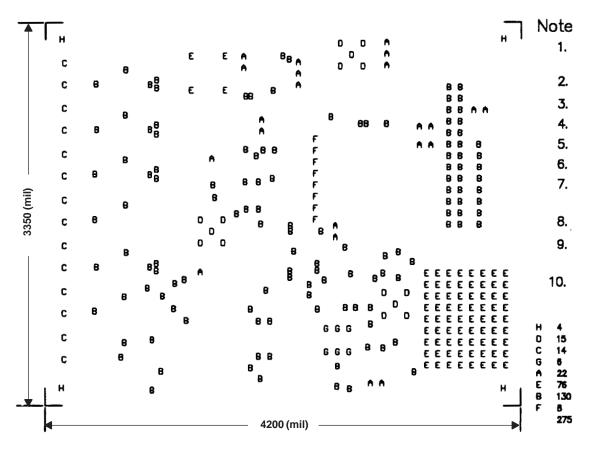
Internal Plane 2

Figure 15. EVM Schematic (Continued)



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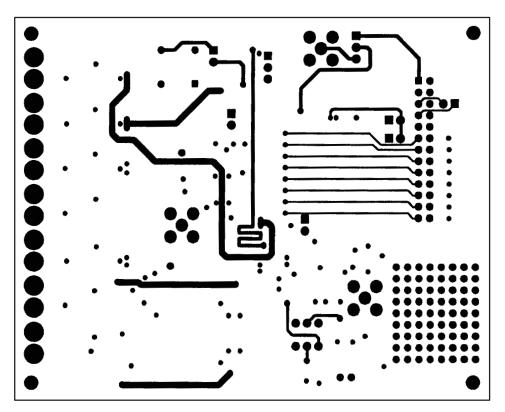




Drill Drawing for Through Hole

Figure 15. EVM Schematic (Continued)





TLV5580 EVALUATION MODULE

Bottom Layer

Figure 15. EVM Schematic (Continued)



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TLV5580 EVALUATION MODULE

Table 3. TLV5580EVM Bill of Material

QTY.	REFERENCE DESIGNATOR	VALUE	SIZE	DESCRIPTION	MANUFACTURER/ PART NUMBER [†]	
7	C1, C11, C13, C3, C5, C7, C9	1 μF	1206	ceramic multi-layer capacitor	Any	
18	C10, C12, C14, C15, C16, C17, C18, C19, C2, C20, C21, C22, C23, C4, C6, C8, C38, C44	10 µF	3216	16 V, 10 μF , tantalum capacitor	Any	
2	C36, C43	0.01 μF	805	Ceramic multi-layer	Any	
19 C24, C25, C26, C27, C28, C29, C30, C31, C32, C33, C34, C35, C37, C39, C40, C41, C42, C45, C46		0.1 μF	805	Ceramic multi-layer capacitor	Any	
7	J1, J2, J3, J4, J5, J6, J7	Screw Con		2 terminal screw connector	Lumberg KRMZ2	
3	J10, J8, J9	SMA		PCM mount, SMA Jack	Johnson Components 142-0701-206	
1	J11	IDC26		$13'' \times 2.025''$ square pin header	Samtec TSW-113-07-L-D	
7	L1, L2, L3, L4, L5, L6, L7	4.7 μΗ		4.7 µH DO1608C-472-Coil Craft	Coil Craft DO1608-472	
1	R2	0	1206	Chip resistor	Any	
2	R26, R27	10	1206	Chip resistor	Any	
12	R1, R11, R14, R40, R41, R42, R43, R44, R45, R46, R47, R48			Chip resistor	Any	
6	R10, R12, R15, R16, R8, R9	1 K	1206	Chip resistor	Any	
1	R5	2.1 K	1206	Chip resistor	Any	
20	R13, R17, R18, R19, R20, R21, R22, R23, R24, R25, R29, R30, R31, R32, R33, R35, R36, R37, R38, R39	20	1206	Chip resistor	Any	
1	R3	200	1206	Chip resistor	Any	
1	R4	3.24 K	1206	Chip resistor	Any	
2	R28, R34	49.9	1206	Chip resistor	Any	
1	R6	5 K		4 mm SM pot-top adjust	Bourns 3214W-5K	
1	R7	1 K		4 mm SM pot-top adjust	Bourns 3214W-1K	
2	SW1, SW2	SPDT		C&K tiny series-slide switch	C&K TS01CLE	
4 TP1, TP2, TP3, TP4		TP		Test point, single 0.025" pin	Samtec TSW-101-07-L-S or equivalent	
1	U3	CXD2306Q			Sony CXD2306Q	
1	U2	SN74ALVC00D	14-SOIC (D)	Quad 2-input positive NAND	Texas Instruments SN74ALVC00D	
1	U5	SN74LVT574DW	20-SOP (DW)		Texas Instruments SN74LVT574DW	

[†] Manufacturer and part number data for reference only. Equivalent parts might be substituted on the EVM.



TLV5580 EVALUATION MODULE

Table 3. TLV5580EVM Bill of Material (Continued)

QTY.	REFERENCE DESIGNATOR	VALUE	SIZE	DESCRIPTION	MANUFACTURER/ PART NUMBER [†]
1	U4	TLE2144CDW	16-SOP(D)	Quad op amp	Texas Instruments TLE2144CDW/ TLE2144IDW
1	U6	TLV5580PW	28-TSSOP (PW)		Texas Instruments TLV5580PW
1	U1	TPS7133	8-SOP(D)	Low-dropout voltage regulator	Texas Instruments TPS7133QD
6	W2, W4, W5, W6, W7, W8	SPST		2 position jumper, 0.1" spacing	Samtec TSW-102-07-L-S or equivalent
2	W1, W3	DPFT		3 position jumper, 0.1" spacing	Samtec TSW-103-07-L-S or equivalent
1	X1	NA		Crystal oscillator	Epson SG-8002DC series

⁺ Manufacturer and part number data for reference only. Equivalent parts might be substituted on the EVM.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV5580CPW	ACTIVE	TSSOP	PW	28	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TV5580	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TEXAS INSTRUMENTS

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TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TLV5580CPW	PW	TSSOP	28	50	530	10.2	3600	3.5

PW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153



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